



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features**

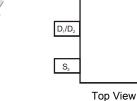
- Low Gate Charge
- Low R<sub>DS(ON)</sub>:
  - 24mΩ @ V<sub>GS</sub> = 4.5V
  - 28mΩ @ V<sub>GS</sub> = 2.5V
  - 34mΩ @ V<sub>GS</sub> = 1.8V
- Low Input/Output Leakage
- ESD Protected up to 2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT26
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.0008 grams (approximate)







G1 G2 N-Channel

N-Channel

Equivalent Circuit

Top View

- 1

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMG6968UDM-7	SOT26	3000/Tape & Reel

Pin Configuration

SOT26

G,

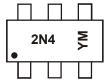
D<sub>1</sub>/D<sub>2</sub>

G,

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



2N4 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009)

M = Month (ex: 9 = September)

Date Code Kev

 ato codo rtoj												
Year	2008		2009	2010		2011	2012	2	2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	20	V
Gate-Source Voltage (Note 5)		$V_{GSS}$	±12	V
Drain Current (Note 6) Continuous	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	6.5 5.2	А
Pulsed Drain Current (Note 7)		I <sub>DM</sub>	30	Α

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	0.85	W
Thermal Resistance, Junction to Ambient (Note 6) t ≤10s	$R_{ hetaJA}$	147	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 5. AEC-Q101 VGS maximum is  $\pm 9.6 \text{V}.$
- 6. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t  $\leq$ 10s. 7. Repetitive Rating, pulse width limited by junction temperature.

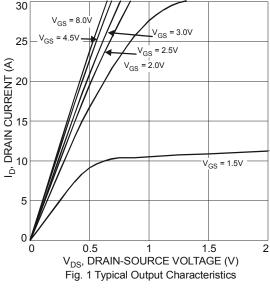
### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

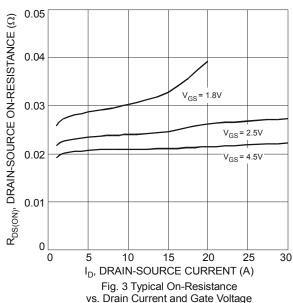
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
STATIC CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20		_	V	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1	μΑ	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V		
Gate-Body Leakage Current	I <sub>GSS</sub>		_	±10	μΑ	$V_{DS} = 0V, V_{GS} = \pm 10V$		
Gate-Source Breakdown Voltage	BV <sub>SGS</sub>	±12	_	_	V	$V_{DS} = 0V, I_G = \pm 250 \mu A$		
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	_	0.9	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA		
Static Drain-Source On-Resistance (Note 8)	R <sub>DS</sub> (ON)	_	17 20 26	24 28 34	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 6.5A V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 5.5A V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 3.5A		
Forward Transfer Admittance	Y <sub>FS</sub>		8	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 5A		
Diode Forward Voltage (Note 8)	$V_{SD}$	_	0.7	1.0	V	I <sub>S</sub> = 2.25A, V <sub>GS</sub> = 0V		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	Ciss	_	143	_	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz		
Output Capacitance	Coss	_	74	_	pF			
Reverse Transfer Capacitance	C <sub>rss</sub>		29	_	pF	1 - 1.0001112		
Gate Resisitance	R <sub>G</sub>		202	_	Ω	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1MHz		
SWITCHING CHARACTERISTICS (Note 9)								
Total Gate Charge	$Q_g$	_	8.8	_	nC			
Gate-Source Charge	$Q_{gs}$		1.4	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.5A$		
Gate-Drain Charge	$Q_{gd}$		3.0	_	nC			
Turn-On Delay Time	t <sub>D(on)</sub>		53	_	ns			
Turn-On Rise Time	t <sub>r</sub>		78	_	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V,		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	562	_	ns	$R_L = 10\Omega$ , $R_G = 6\Omega$		
Turn-Off Fall Time	t <sub>f</sub>		234	_	ns	]		

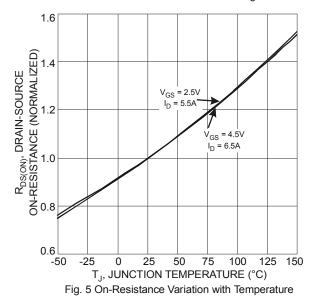
Notes:

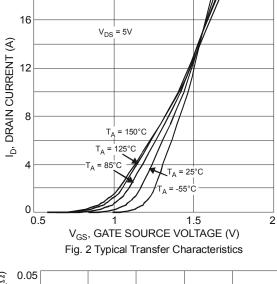
- 8. Test pulse width t = 300ms.
- 9. Guaranteed by design. Not subject to production testing.











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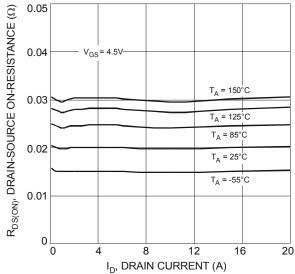


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

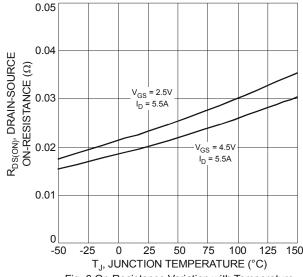


Fig. 6 On-Resistance Variation with Temperature



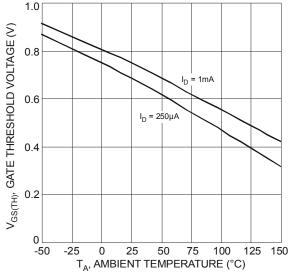
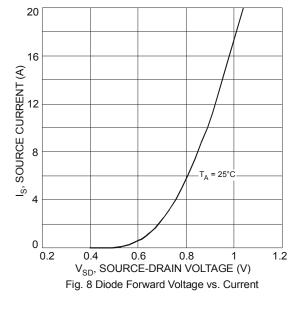
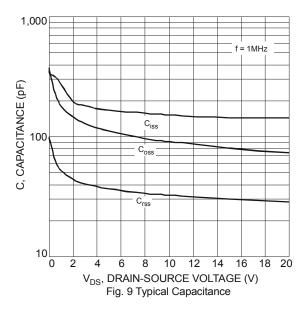
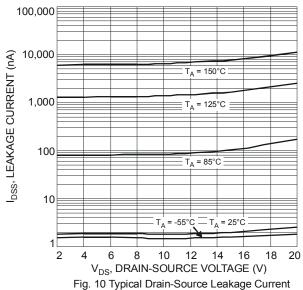


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







vs. Drain-Source Voltage

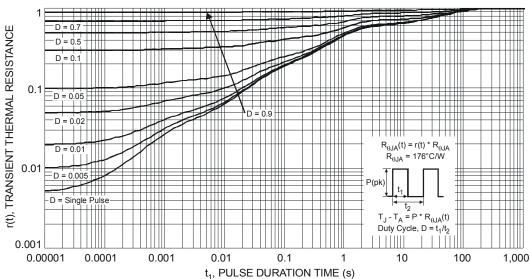
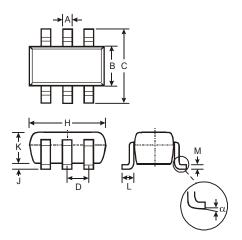


Fig. 11 Transient Thermal Response



### **Package Outline Dimensions**

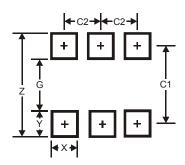
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26							
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	_	_	0.95				
Н	2.90	3.10	3.00				
<b>J</b> 0.013		0.10	0.05				
K	1.00	1.30	1.10				
L	0.35	0.55	0.40				
М	0.10	0.20	0.15				
α 0°		8°	_				
All D	All Dimensions in mm						

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95



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